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ONS00470
10/773,853Remarks

Claims 1-20 are in the application.

By this amendment, claims 1, 2, 3, 5, 6, 8, 10, 11, 17, and 18 have been amended to more clearly set out applicant's invention. Applicant respectfully submits that no new matter has been added, and that his specification supports the changes made.

Response to 35 U.S.C. §103(a) Rejection

Claims 1-20 were rejected under 35 U.S.C. §103(a) as being unpatentable over Wieczorek et al., USP 6,821,840, (hereinafter "Wieczorek"). This rejection is respectfully traversed in view of the amendments made herein and the remarks presented hereafter.

Claim 1 calls for a method for forming an isolation region comprising the steps of providing a region of semiconductor material. The also calls for forming a tub in the region of semiconductor material, wherein the tub includes a plurality of shapes. The method further calls for exposing the plurality of shapes to an ambient that includes a chemical species that reacts with the plurality shapes to form the isolation region, and wherein the plurality of shapes form part of the isolation region.

Applicant respectfully submits that Wieczorek fails to make claim 1 obvious because Wieczorek does not show or suggest a method of forming an isolation region including forming a tub with a plurality of shapes, and exposing the plurality of shapes to an ambient that includes a chemical species that reacts with the plurality of shapes to form the isolation region. Specifically, Wieczorek is completely silent as to how isolation regions 102 and 202 are formed, and there is no suggestion of the

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method set forth in applicant's claim 1. For at least these reasons, applicant respectfully submits that claim 1 is allowable over Wieczorek.

Claims 2-9 depend from claim 1 and are believed allowable for at least the same reasons as claim 1.

Claim 10 calls for, a process for forming an integrated circuit device including forming a tub region within a semiconductor layer, wherein tub region includes a matrix of shapes comprising offset rows. The method further calls for forming a dielectric region within the matrix of shapes.

Applicant respectfully submits that Wieczorek fails to make claim 10 obvious because Wieczorek does not show or suggest a method including forming a tub region within a semiconductor layer, wherein the tub region includes matrix of shapes comprising offset rows. Specifically, Wieczorek is completely silent as to how regions 102 and 202 are formed, and there is no suggestion of the method set forth in applicant's claim 10. For at least these reasons, applicant respectfully submits that claim 10 is allowable over Wieczorek.

Claims 11-17 depend from claim 10 and are believed allowable for at least the same reasons as claim 10.

Claim 18 calls for a semiconductor device including a region of semiconductor material. A dielectric tub is formed in the region of semiconductor material, wherein the dielectric tub includes a matrix of passivated shapes, and wherein adjacent rows of passivated shapes are offset.

Applicant respectfully submits that claim 18 is allowable over Wieczorek because the cited reference does not show or suggest a dielectric tub formed in a region of semiconductor material, which includes a matrix of passivated shapes, and wherein adjacent rows of passivated shapes are offset. Specifically, there is no evidence of any matrix of passivated shapes within Wieczorek's dielectric regions 102 and 202, and

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there is no suggestion in Wieczorek's specification to use a matrix of passivated shapes. Thus, for at least these reasons, applicant respectfully submits that claim 18 is allowable over Wieczorek.

Claims 19-20 depend from claim 18 and are believed allowable for at least the same reasons as claim 18.

In view of all of the above, it is believed that the claims are allowable, and the case is now in condition for allowance, which action is earnestly solicited.

Respectfully submitted,

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